



VN5E160MS-E

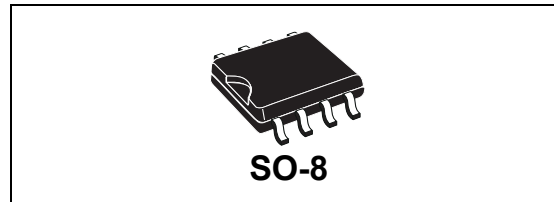
Single-channel high-side driver with analog for automotive applications

Features

| | | |
|-----------------------------------|------------|--------------------------|
| Max supply voltage | V_{CC} | 41 V |
| Operating voltage range | V_{CC} | 4.5 V to 28 V |
| Max ON-state resistance (per ch.) | R_{ON} | 160 m Ω |
| Current limitation (typ) | I_{LIMH} | 10 A |
| OFF-state supply current | I_S | 2 μ A ⁽¹⁾ |

1. Typical value with all loads connected.

- General
 - Inrush current active management by power limitation
 - Very low standby current
 - 3.0 V CMOS compatible inputs
 - Optimized electromagnetic emission
 - Very low electromagnetic susceptibility
 - In compliance with the 2002/95/EC european directive
 - Very low current sense leakage
- Diagnostic functions
 - Proportional load current sense
 - High-precision current sense for wide currents range
 - Current sense disable
 - Overload and short to ground (power limitation) indication
 - Thermal shutdown indication
- Protections
 - Undervoltage shutdown
 - Overvoltage clamp
 - Load current limitation
 - Self-limiting of fast thermal transients
 - Protection against loss of ground and loss of V_{CC}
 - Overtemperature shutdown with autorestart (thermal shutdown)
 - Reverse battery protected (see [Figure 29](#))



- Electrostatic discharge protection

Applications

- All types of resistive, inductive and capacitive loads
- Suitable as LED driver

Description

The VN5E160MS-E is a single-channel high-side driver manufactured in the ST proprietary VIPower M0-5 technology and housed in the tiny SO-8 package. The VN5E160MS-E is designed to drive 12 V automotive grounded loads delivering protection, diagnostics and easy 3 V and 5 V CMOS compatible interface with any microcontroller.

The device integrates advanced protective functions such as load current limitation, inrush and overload active management by power limitation, overtemperature shut-off with auto-restart and overvoltage active clamp. A dedicated analog current sense pin is associated with every output channel in order to provide enhanced diagnostic functions including fast detection of overload and short-circuit to ground through power limitation indication and overtemperature indication.

The current sensing and diagnostic feedback of the whole device can be disabled by pulling the CS_DIS pin high to allow sharing of the external sense resistor with other similar devices.

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1 Block diagram and pin configuration

Figure 1. Block diagram

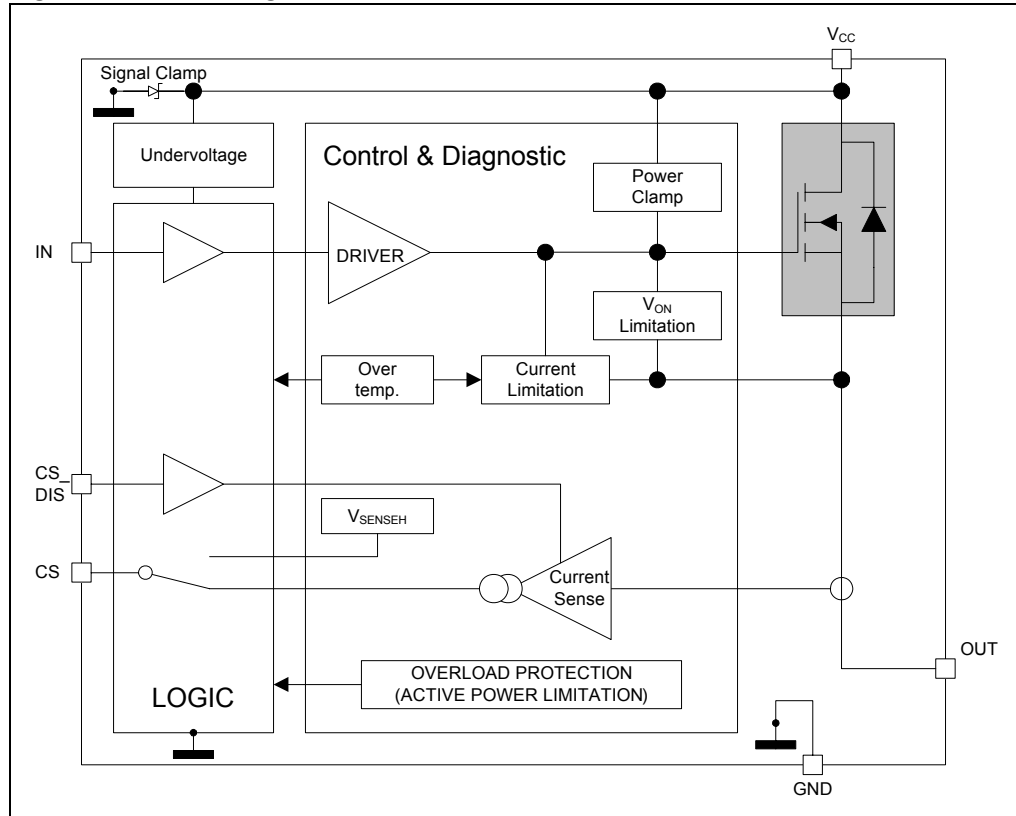


Table 1. Pin function

| Name | Function |
|-----------------|---|
| V _{CC} | Battery connection |
| OUT | Power output |
| GND | Ground connection. Must be reverse battery protected by an external diode/resistor network |
| IN | Voltage-controlled input pin with hysteresis, CMOS compatible. Controls output switch state |
| CS | Analog current sense pin, delivers a current proportional to the load current |
| CS_DIS | Active high CMOS compatible pin, to disable the current sense pin |

Figure 2. Configuration diagram (top view)

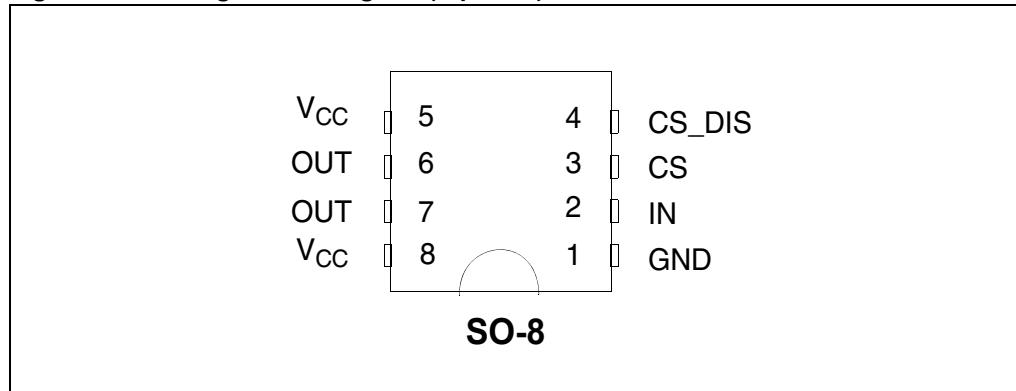
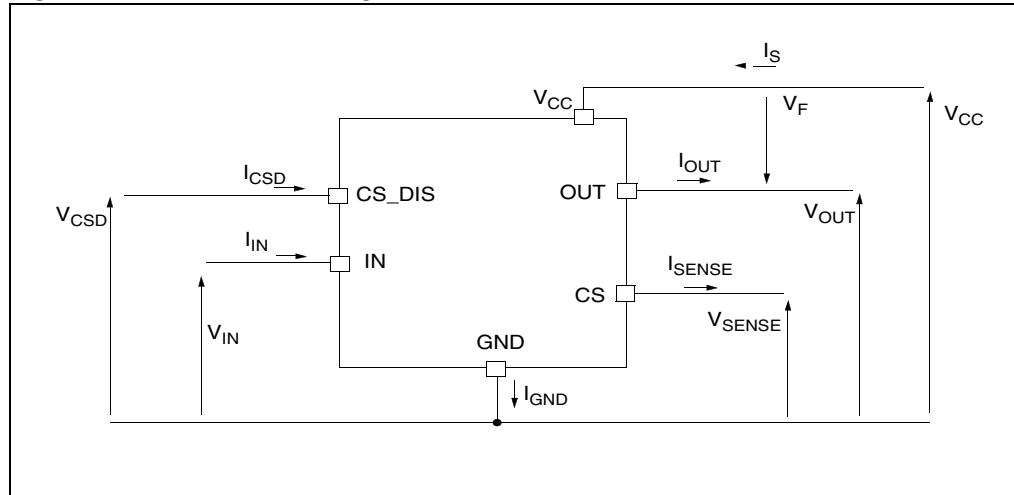


Table 2. Suggested connections for unused and not connected pins

| Connection / pin | Current sense | N.C. | Output | Input | CS_DIS |
|------------------|-------------------------------|------|-------------|--------------------------------|--------------------------------|
| Floating | Not allowed | X | X | X | X |
| To ground | Through 1 k Ω resistor | X | Not allowed | Through 10 k Ω resistor | Through 10 k Ω resistor |

2 Electrical specifications

Figure 3. Current and voltage conventions⁽¹⁾



1. $V_F = V_{OUT} - V_{CC}$ during reverse battery condition.

2.1 Absolute maximum ratings

Stressing the device above the ratings listed in the [Table 3: Absolute maximum ratings](#) may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to the conditions in the [Table 3: Absolute maximum ratings](#) for extended periods may affect device reliability. Refer also to the STMicroelectronics SURE program and other relevant quality documents.

Table 3. Absolute maximum ratings

| Symbol | Parameter | Value | Unit |
|---------------|--|----------------------------|--------|
| V_{CC} | DC supply voltage | 41 | V |
| $-V_{CC}$ | Reverse DC supply voltage | 0.3 | V |
| $-I_{GND}$ | DC reverse ground pin current | 200 | mA |
| I_{OUT} | DC output current | Internally limited | A |
| $-I_{OUT}$ | Reverse DC output current | 6 | A |
| I_{IN} | DC input current | -1 to 10 | mA |
| I_{CSD} | DC current sense disable input current | -1 to 10 | mA |
| $-I_{CSENSE}$ | DC reverse CS pin current | 200 | mA |
| V_{CSENSE} | Current sense maximum voltage | $V_{CC} - 41$ $+V_{CC}$ | V V |

Table 3. Absolute maximum ratings (continued)

| Symbol | Parameter | Value | Unit |
|-----------|--|------------|------------------|
| E_{MAX} | Maximum switching energy (single pulse) ($L = 8 \text{ mH}$; $R_L = 0 \text{ }\Omega$; $V_{bat} = 13.5 \text{ V}$; $T_{jstart} = 150 \text{ }^\circ\text{C}$; $I_{OUT} = I_{limL}(\text{Typ.})$) | 36 | mJ |
| V_{ESD} | Electrostatic discharge (human body model: $R = 1.5 \text{ K}\Omega$; $C = 100 \text{ pF}$) | | |
| | - IN | 4000 | V |
| | - CS | 2000 | V |
| | - CS_DIS | 4000 | V |
| | - OUT | 5000 | V |
| | - V_{CC} | 5000 | V |
| V_{ESD} | Charge device model (CDM-AEC-Q100-011) | 750 | V |
| T_j | Junction operating temperature | -40 to 150 | $^\circ\text{C}$ |
| T_{stg} | Storage temperature | -55 to 150 | $^\circ\text{C}$ |

2.2 Thermal data

Table 4. Thermal data

| Symbol | Parameter | Max value | Unit |
|----------------|-------------------------------------|-------------------------------|--------------------|
| $R_{thj-pins}$ | Thermal resistance junction-pins | 30 | $^\circ\text{C/W}$ |
| $R_{thj-amb}$ | Thermal resistance junction-ambient | See Figure 33 | $^\circ\text{C/W}$ |

2.3 Electrical characteristics

Values specified in this section are for $8\text{ V} < V_{CC} < 28\text{ V}$; $-40\text{ °C} < T_j < 150\text{ °C}$, unless otherwise stated.

Table 5. Power section

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|----------------------------------|---|------|------------------|------------------|------|
| V_{CC} | Operating supply voltage | | 4.5 | 13 | 28 | V |
| V_{USD} | Undervoltage shutdown | | | 3.5 | 4.5 | V |
| $V_{USDhyst}$ | Undervoltage shutdown hysteresis | | | 0.5 | | V |
| R_{ON} | ON-state resistance | $I_{OUT} = 1\text{ A}$, $T_j = 25\text{ °C}$ | | | 160 | mΩ |
| | | $I_{OUT} = 1\text{ A}$, $T_j = 150\text{ °C}$ | | | 320 | |
| | | $I_{OUT} = 1\text{ A}$, $V_{CC} = 5\text{ V}$, $T_j = 25\text{ °C}$ | | | 210 | |
| V_{clamp} | Voltage clamp | $I_S = 20\text{ mA}$ | 41 | 46 | 52 | V |
| I_S | Supply current | OFF-state: $V_{CC} = 13\text{ V}$, $V_{IN} = V_{OUT} = 0\text{ V}$, $T_j = 25\text{ °C}$ | | 2 ⁽¹⁾ | 5 ⁽¹⁾ | μA |
| | | ON-state: $V_{IN} = 5\text{ V}$, $V_{CC} = 13\text{ V}$, $I_{OUT} = 0\text{ A}$ | | 1.9 | 3.5 | mA |
| $I_{L(off1)}$ | OFF-state output current | $V_{IN} = V_{OUT} = 0\text{ V}$, $V_{CC} = 13\text{ V}$, $T_j = 25\text{ °C}$ | 0 | 0.01 | 3 | μA |
| | | $V_{IN} = V_{OUT} = 0\text{ V}$, $V_{CC} = 13\text{ V}$, $T_j = 125\text{ °C}$ | 0 | | 5 | |
| V_F | Output - V_{CC} diode voltage | $-I_{OUT} = 1\text{ A}$, $T_j = 150\text{ °C}$ | | | 0.7 | V |

1. PowerMOS leakage included.

Table 6. Switching ($V_{CC} = 13\text{ V}$; $T_j = 25\text{ °C}$)

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------------|---|--|------|-------------------------------|------|------|
| $t_{d(on)}$ | Turn-on delay time | $R_L = 13\text{ Ω}$ (see Figure 5) | - | 10 | - | μs |
| $t_{d(off)}$ | Turn-off delay time | $R_L = 13\text{ Ω}$ (see Figure 5) | - | 10 | - | μs |
| $dV_{OUT}/dt_{(on)}$ | Turn-on voltage slope | $R_L = 13\text{ Ω}$ | - | See Figure 23 | - | V/μs |
| $dV_{OUT}/dt_{(off)}$ | Turn-off voltage slope | $R_L = 13\text{ Ω}$ | - | See Figure 25 | - | V/μs |
| W_{ON} | Switching energy losses during t_{won} | $R_L = 13\text{ Ω}$ (see Figure 5) | - | 0.05 | - | mJ |
| W_{OFF} | Switching energy losses during t_{woff} | $R_L = 13\text{ Ω}$ (see Figure 5) | - | 0.03 | - | mJ |

Table 7. Logic inputs

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------|---------------------------|--------------------------|------|------|------|---------------|
| V_{IL} | Low-level input voltage | | | | 0.9 | V |
| I_{IL} | Low-level input current | $V_{IN} = 0.9\text{ V}$ | 1 | | | μA |
| V_{IH} | High-level input voltage | | 2.1 | | | V |
| I_{IH} | High-level input current | $V_{IN} = 2.1\text{ V}$ | | | 10 | μA |
| $V_{I(hyst)}$ | Input voltage hysteresis | | 0.25 | | | V |
| V_{ICL} | Input voltage clamp | $I_{IN} = 1\text{ mA}$ | 5.5 | | 7 | V |
| | | $I_{IN} = -1\text{ mA}$ | | -0.7 | | |
| V_{CSDL} | Low-level CS_DIS voltage | | | | 0.9 | V |
| I_{CSDL} | Low-level CS_DIS current | $V_{CSD} = 0.9\text{ V}$ | 1 | | | μA |
| V_{CSDH} | High-level CS_DIS voltage | | 2.1 | | | V |
| I_{CSDH} | High-level CS_DIS current | $V_{CSD} = 2.1\text{ V}$ | | | 10 | μA |
| $V_{CSD(hyst)}$ | CS_DIS voltage hysteresis | | 0.25 | | | V |
| V_{CSCL} | CS_DIS voltage clamp | $I_{CSD} = 1\text{ mA}$ | 5.5 | | 7 | V |
| | | $I_{CSD} = -1\text{ mA}$ | | -0.7 | | |

Table 8. Protection and diagnostics⁽¹⁾

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-------------|--|--|---------------|---------------|---------------|--------------------|
| I_{limH} | DC short-circuit current | $V_{CC} = 13\text{ V}$ | 7 | 10 | 14 | A |
| | | $5\text{ V} < V_{CC} < 28\text{ V}$ | | | 14 | A |
| I_{limL} | Short-circuit current during thermal cycling | $V_{CC} = 13\text{ V}$ $T_R < T_J < T_{TSD}$ | | 2.5 | | A |
| T_{TSD} | Shutdown temperature | | 150 | 175 | 200 | $^{\circ}\text{C}$ |
| T_R | Reset temperature | | $T_{RS} + 1$ | $T_{RS} + 5$ | | $^{\circ}\text{C}$ |
| T_{RS} | Thermal reset of STATUS | | 135 | | | $^{\circ}\text{C}$ |
| T_{HYST} | Thermal hysteresis ($T_{TSD} - T_R$) | | | 7 | | $^{\circ}\text{C}$ |
| V_{DEMAG} | Turn-off output voltage clamp | $I_{OUT} = 1\text{ A}$, $V_{IN} = 0$, $L = 20\text{ mH}$ | $V_{CC} - 41$ | $V_{CC} - 46$ | $V_{CC} - 52$ | V |
| V_{ON} | Output voltage drop limitation | $I_{OUT} = 0.03\text{ A}$ (see Figure 8) $T_J = -40\text{ }^{\circ}\text{C}$ to $+150\text{ }^{\circ}\text{C}$ | | 25 | | mV |

1. To ensure long term reliability under heavy overload or short-circuit conditions, protection and related diagnostic signals must be used together with a proper software strategy. If the device is subjected to abnormal conditions, this software must limit the duration and number of activation cycles.

Table 9. Current sense ($8\text{ V} < V_{CC} < 18\text{ V}$)

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|--------------------|---|---|------------|------------|------------|---------------|
| K_0 | I_{OUT}/I_{SENSE} | $I_{OUT} = 0.025\text{ A}$, $V_{SENSE} = 0.5\text{ V}$ $T_j = -40\text{ }^\circ\text{C}$ to $150\text{ }^\circ\text{C}$ | 265 | 490 | 715 | |
| K_1 | I_{OUT}/I_{SENSE} | $I_{OUT} = 0.35\text{ A}$, $V_{SENSE} = 0.5\text{ V}$ $T_j = -40\text{ }^\circ\text{C}$ to $150\text{ }^\circ\text{C}$ $T_j = 25\text{ }^\circ\text{C}$ to $150\text{ }^\circ\text{C}$ | 355 385 | 465 465 | 575 545 | |
| $dK_1/K_1^{(1)}$ | Current sense ratio drift | $I_{OUT} = 0.35\text{ A}$, $V_{SENSE} = 0.5\text{ V}$ $T_j = -40\text{ }^\circ\text{C}$ to $150\text{ }^\circ\text{C}$ | -11 | | +11 | % |
| K_2 | I_{OUT}/I_{SENSE} | $I_{OUT} = 0.5\text{ A}$, $V_{SENSE} = 4\text{ V}$ $T_j = -40\text{ }^\circ\text{C}$ to $150\text{ }^\circ\text{C}$ $T_j = 25\text{ }^\circ\text{C}$ to $150\text{ }^\circ\text{C}$ | 380 400 | 455 455 | 530 510 | |
| $dK_2/K_2^{(1)}$ | Current sense ratio drift | $I_{OUT} = 0.5\text{ A}$; $T_j = -40\text{ }^\circ\text{C}$ to $150\text{ }^\circ\text{C}$ | -8 | | +8 | % |
| K_3 | I_{OUT}/I_{SENSE} | $I_{OUT} = 1.5\text{ A}$, $V_{SENSE} = 4\text{ V}$ $T_j = -40\text{ }^\circ\text{C}$ to $150\text{ }^\circ\text{C}$ $T_j = 25\text{ }^\circ\text{C}$ to $150\text{ }^\circ\text{C}$ | 420 420 | 455 455 | 490 480 | |
| $dK_3/K_3^{(1)}$ | Current sense ratio drift | $I_{OUT} = 1.5\text{ A}$; $T_j = -40\text{ }^\circ\text{C}$ to $150\text{ }^\circ\text{C}$ | -4 | | +4 | % |
| I_{SENSE0} | Analog sense leakage current | $I_{OUT} = 0\text{ A}$, $V_{SENSE} = 0\text{ V}$, $V_{CSD} = 5\text{ V}$, $V_{IN} = 0\text{ V}$, $T_j = -40\text{ }^\circ\text{C}$ to $150\text{ }^\circ\text{C}$ | 0 | | 1 | μA |
| | | $I_{OUT} = 0\text{ A}$, $V_{SENSE} = 0\text{ V}$, $V_{CSD} = 0\text{ V}$, $V_{IN} = 5\text{ V}$, $T_j = -40\text{ }^\circ\text{C}$ to $150\text{ }^\circ\text{C}$ | 0 | | 2 | |
| | | $I_{OUT} = 1\text{ A}$, $V_{SENSE} = 0\text{ V}$, $V_{CSD} = 5\text{ V}$, $V_{IN} = 5\text{ V}$, $T_j = -40\text{ }^\circ\text{C}$ to $150\text{ }^\circ\text{C}$ | 0 | | 1 | |
| I_{OL} | ON-state open-load current detection threshold | $V_{IN} = 5\text{ V}$, $8\text{ V} < V_{CC} < 18\text{ V}$ $I_{SENSE} = 5\text{ } \mu\text{A}$ | 0.5 | | 5 | mA |
| V_{SENSE} | Max analog sense output voltage | $R_{SENSE} = 10\text{ K}\Omega$ $I_{OUT} = 1\text{ A}$; | 5 | | | V |
| $V_{SENSEH}^{(2)}$ | Analog sense output voltage in fault condition | $V_{CC} = 13\text{ V}$, $R_{SENSE} = 3.9\text{ K}\Omega$ | | 8 | | V |
| $I_{SENSEH}^{(2)}$ | Analog sense output current in fault condition | $V_{CC} = 13\text{ V}$, $V_{SENSE} = 5\text{ V}$ | | 9 | | mA |
| $t_{DSENSE1H}$ | Delay response time from falling edge of CS_DIS pin | $V_{SENSE} < 4\text{ V}$, $0.025\text{ A} < I_{OUT} < 1.5\text{ A}$ $I_{SENSE} = 90\%$ of $I_{SENSE\text{ max}}$ (see Figure 4) | | 40 | 100 | μs |

Table 9. Current sense (8 V < V_{CC} < 18 V) (continued)

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|------------------------|--|--|------|------|------|------|
| t _{DSENSE1L} | Delay response time from rising edge of CS_DIS pin | V _{SENSE} < 4 V, 0.025 A < I _{OUT} < 1.5 A I _{SENSE} = 10% of I _{SENSE max} (see Figure 4) | | 5 | 20 | μs |
| t _{DSENSE2H} | Delay response time from rising edge of IN pin | V _{SENSE} < 4 V, 0.025 A < I _{OUT} < 1.5 A I _{SENSE} =90% of I _{SENSE max} (see Figure 4) | | 120 | 300 | μs |
| Δt _{DSENSE2H} | Delay response time between rising edge of output current and rising edge of current sense | V _{SENSE} < 4 V, I _{SENSE} = 90% of I _{SENSEMAX} , I _{OUT} = 90% of I _{OUTMAX} I _{OUTMAX} =1.5A (see Figure 7) | | | 110 | μs |
| t _{DSENSE2L} | Delay response time from falling edge of IN pin | V _{SENSE} < 4 V, 0.025 A < I _{OUT} < 1.5 A I _{SENSE} =10% of I _{SENSE max} (see Figure 4) | | 80 | 250 | μs |

1. Parameter guaranteed by design; it is not tested.
2. Fault condition includes: power limitation and overtemperature.

Figure 4. Current sense delay characteristics

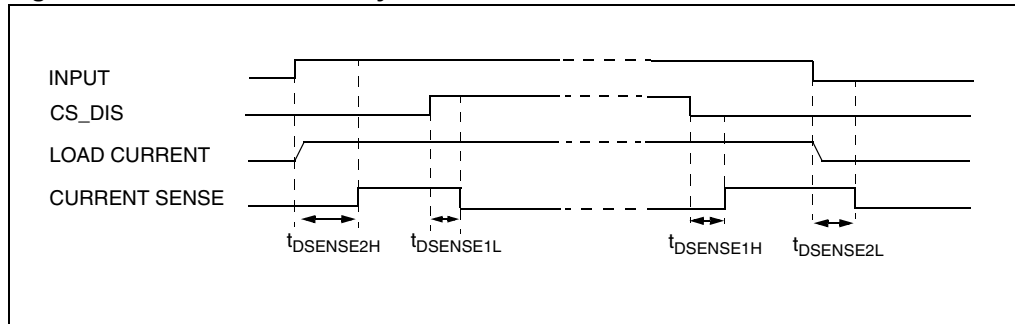


Figure 5. Switching characteristics

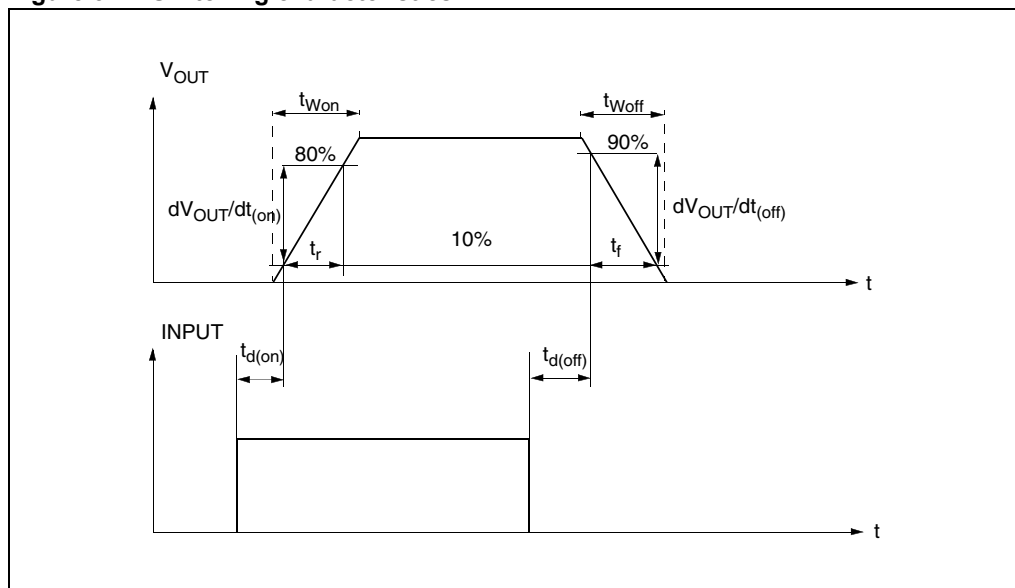


Figure 6. Output voltage drop limitation

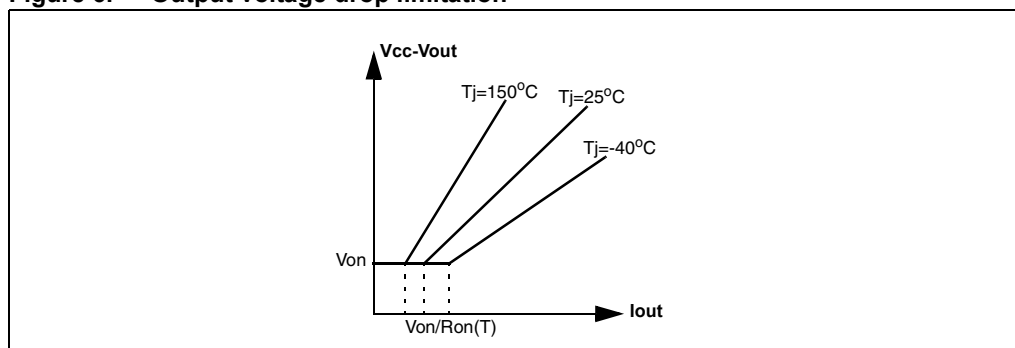


Figure 7. Delay response time between rising edge of output current and rising edge of current sense (CS enabled)

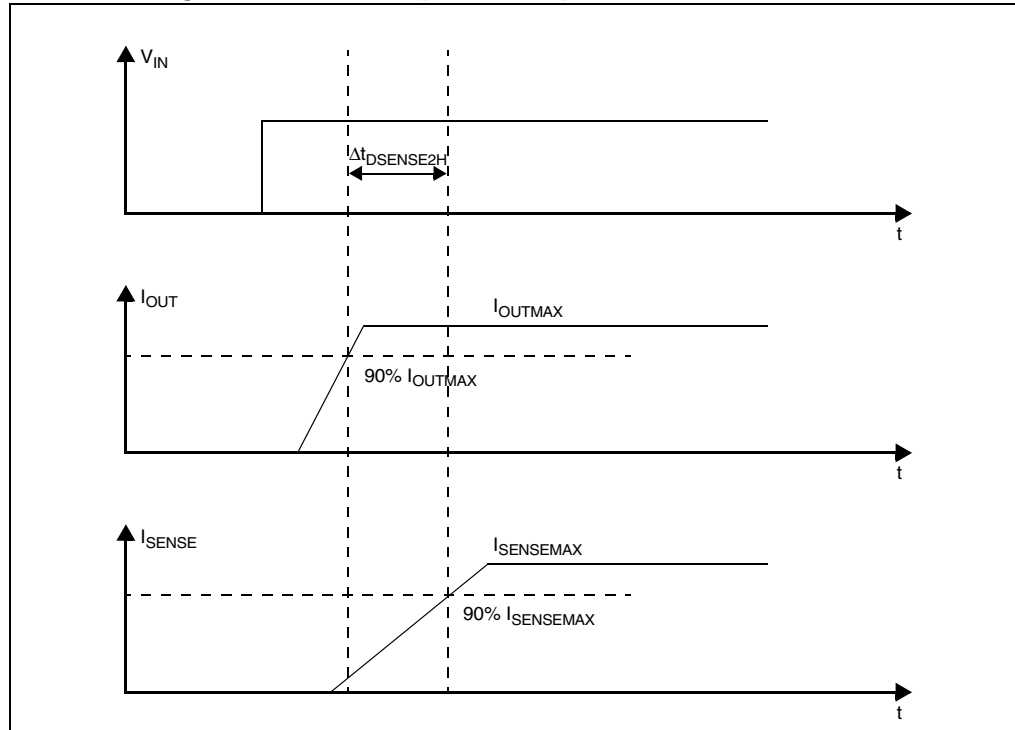


Figure 8. I_{OUT}/I_{SENSE} vs I_{OUT}

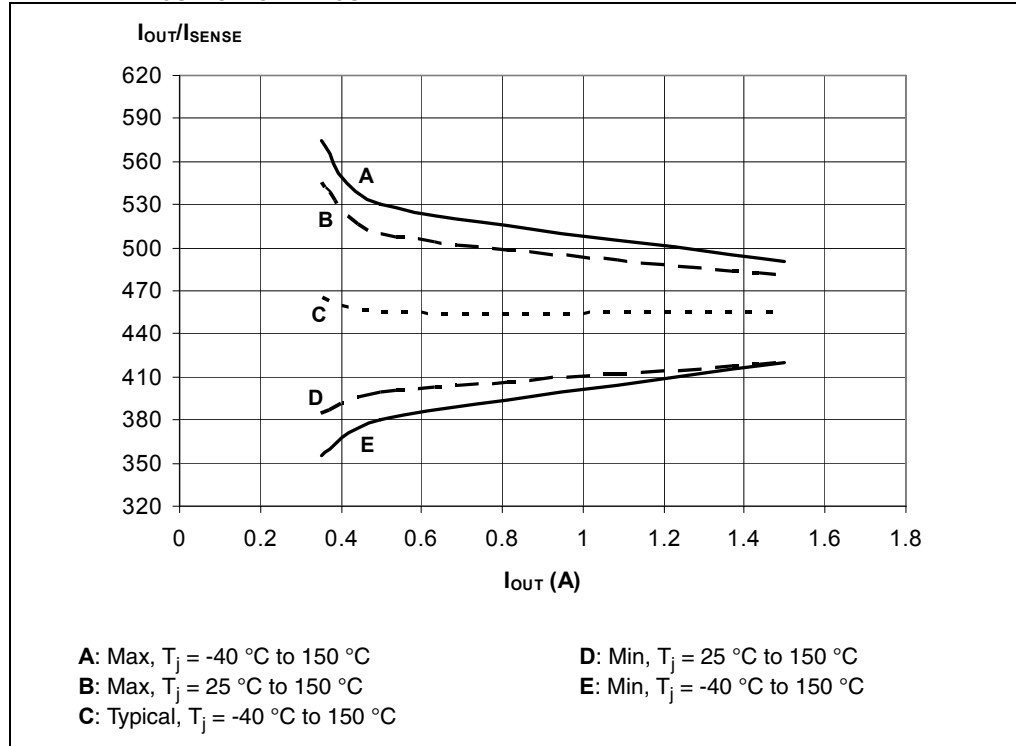
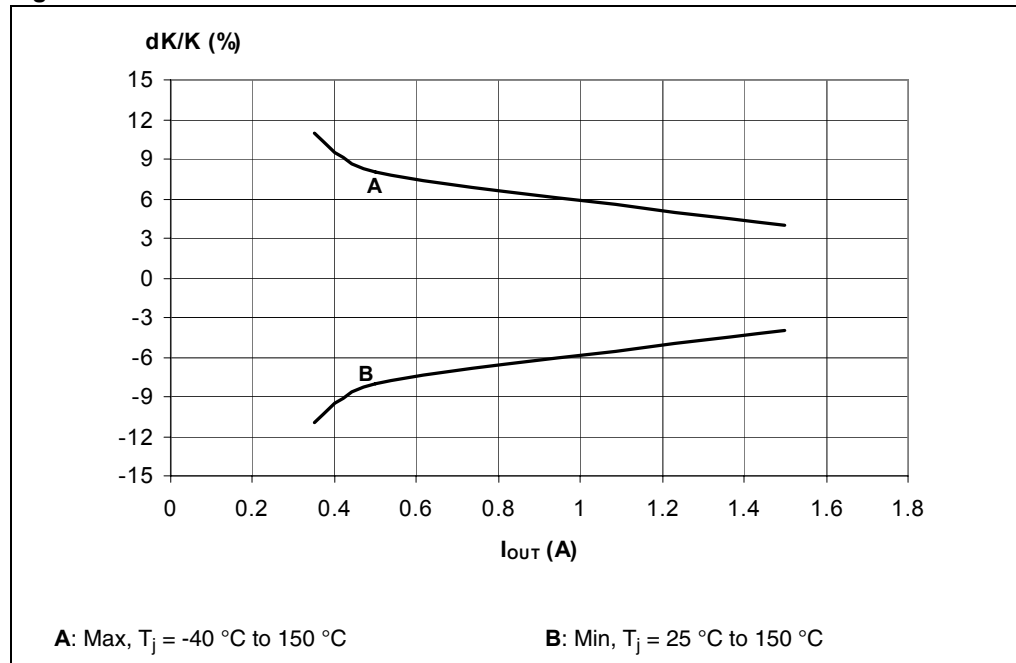


Figure 9. Maximum current sense ratio drift vs load current⁽¹⁾



1. Parameter guaranteed by design; it is not tested.

Table 10. Truth table

| Conditions | IN | OUT | SENSE ($V_{CSD} = 0\text{ V}$) ⁽¹⁾ |
|--|----|-------------------------------|---|
| Normal operation | L | L | 0 |
| | H | H | Nominal |
| Overtemperature | L | L | 0 |
| | H | L | V_{SENSEH} |
| Undervoltage | L | L | 0 |
| | H | L | 0 |
| Overload | H | X (no power limitation) | Nominal |
| | H | Cycling (power limitation) | V_{SENSEH} |
| Short-circuit to GND (Power limitation) | L | L | 0 |
| | H | L | V_{SENSEH} |
| Negative output voltage clamp | L | L | 0 |

1. If the V_{CSD} is high, the SENSE output is at a high impedance, its potential depends on leakage currents and external circuit.

Table 11. Electrical transient requirements (part 1)

| ISO 7637-2: 2004(E) Test pulse | Test levels ⁽¹⁾ | | Number of pulses or test times | Burst cycle/pulse repetition time | | Delays and Impedance |
|--------------------------------------|----------------------------|--------|--------------------------------------|--------------------------------------|--------|--------------------------|
| | III | IV | | | | |
| 1 | -75 V | -100 V | 5000 pulses | 0.5 s | 5 s | 2 ms, 10 Ω |
| 2a | +37 V | +50 V | 5000 pulses | 0.2 s | 5 s | 50 μ s, 2 Ω |
| 3a | -100 V | -150 V | 1h | 90 ms | 100 ms | 0.1 μ s, 50 Ω |
| 3b | +75 V | +100 V | 1h | 90 ms | 100 ms | 0.1 μ s, 50 Ω |
| 4 | -6 V | -7 V | 1 pulse | | | 100 ms, 0.01 Ω |
| 5b ⁽²⁾ | +65 V | +87 V | 1 pulse | | | 400 ms, 2 Ω |

Table 12. Electrical transient requirements (part 2)

| ISO 7637-2: 2004(E) Test pulse | Test level results ⁽¹⁾ | |
|--------------------------------------|-----------------------------------|----|
| | III | IV |
| 1 | C | C |
| 2a | C | C |
| 3a | C | C |
| 3b | C | C |
| 4 | C | C |
| 5b ⁽²⁾ | C | C |

1. The above test levels must be considered referred to $V_{CC} = 13.5$ V except for pulse 5b

2. Valid in case of external load dump clamp: 40 V maximum referred to ground.

Table 13. Electrical transient requirements (part 3)

| Class | Contents |
|-------|--|
| C | All functions of the device are performed as designed after exposure to disturbance. |
| E | One or more functions of the device are not performed as designed after exposure to disturbance and cannot be returned to proper operation without replacing the device. |

2.4 Waveforms

Figure 10. Normal operation

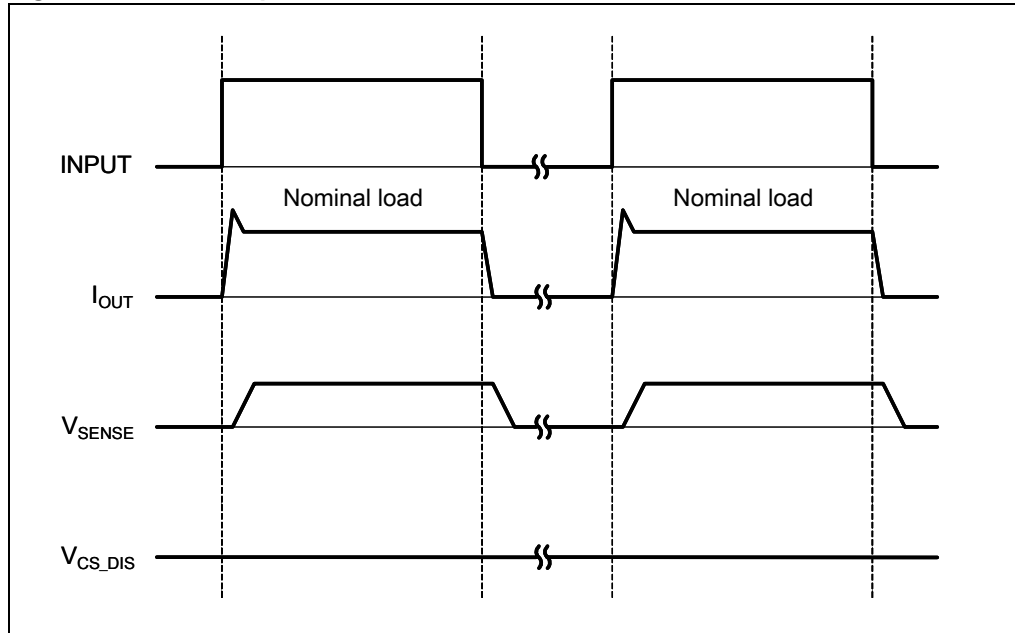


Figure 11. Overload or short to GND

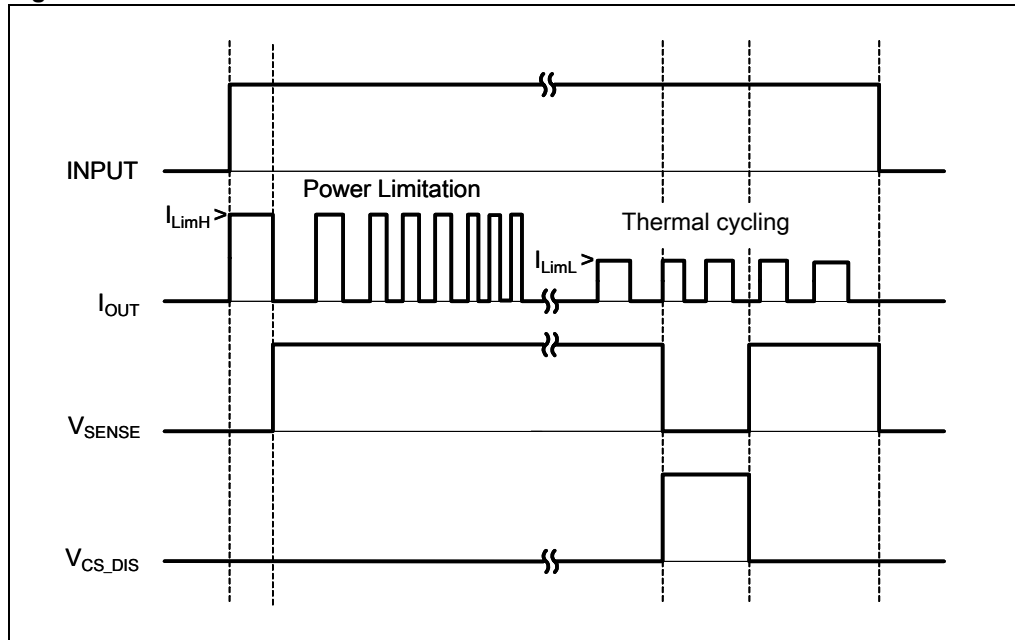


Figure 12. Intermittent overload

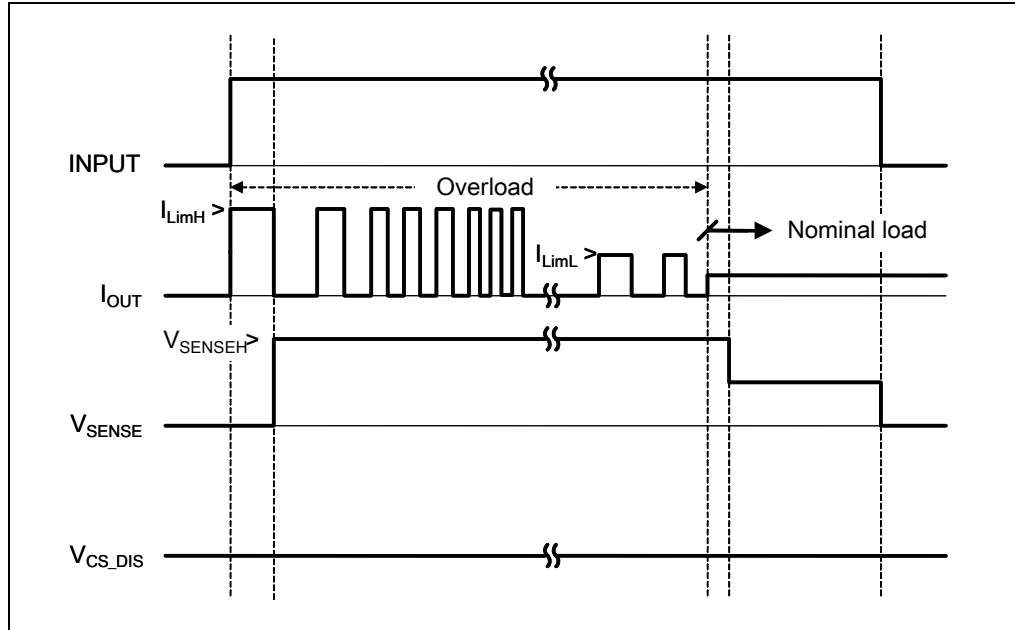
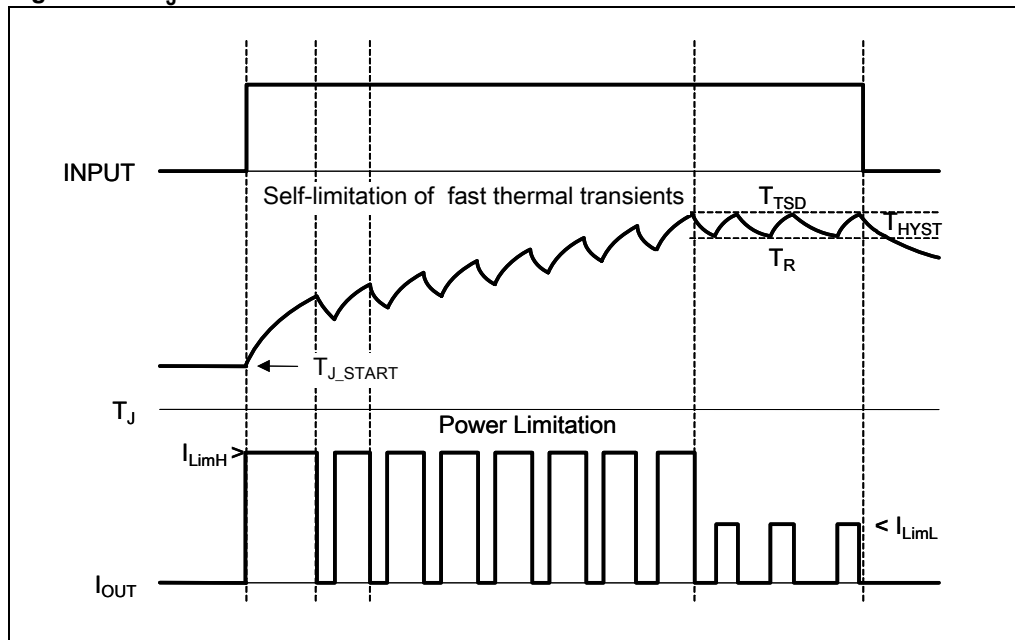


Figure 13. T_J evolution in overload or short to GND



2.5 Electrical characteristics curves

Figure 14. OFF-state output current

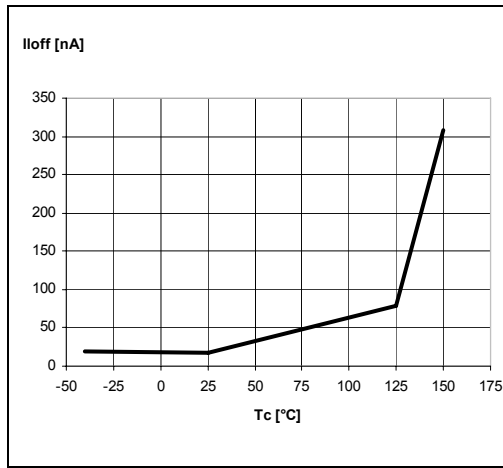


Figure 15. High-level input current

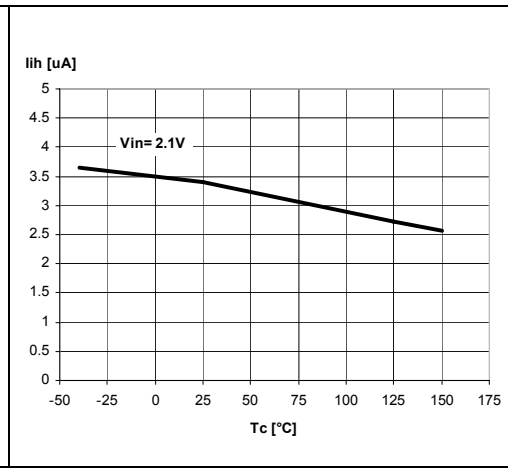


Figure 16. Input voltage clamp

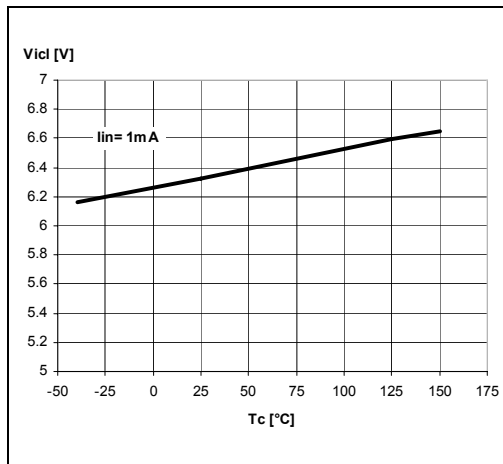


Figure 17. Low-level input voltage

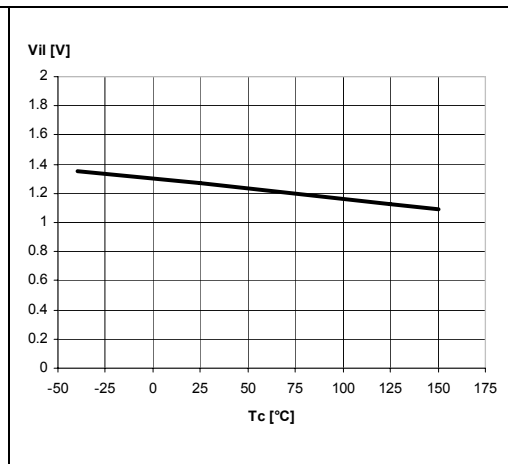


Figure 18. High-level input voltage

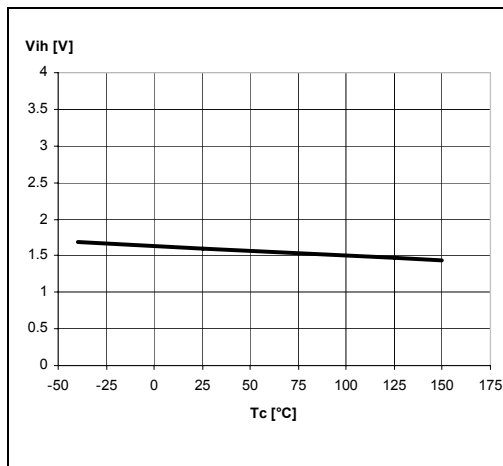


Figure 19. Hysteresis input voltage

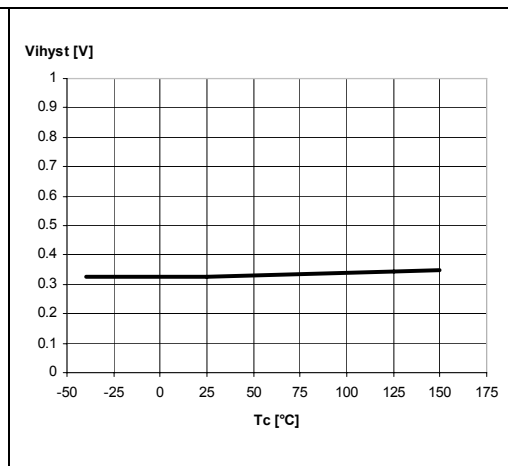


Figure 20. ON-state resistance vs. T_{case}

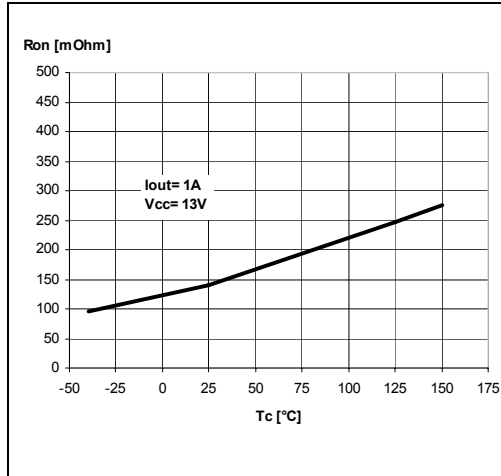


Figure 21. ON-state resistance vs. V_{CC}

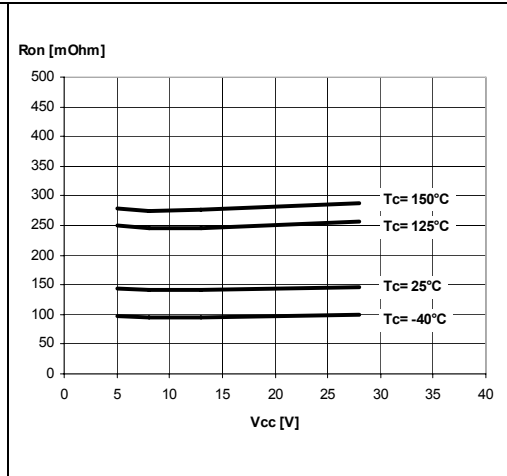


Figure 22. Undervoltage shutdown

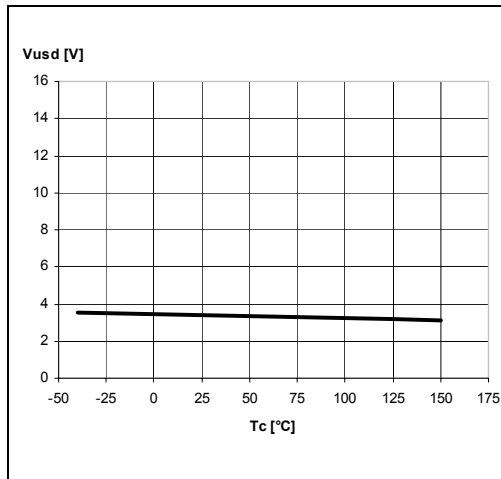


Figure 23. Turn-on voltage slope

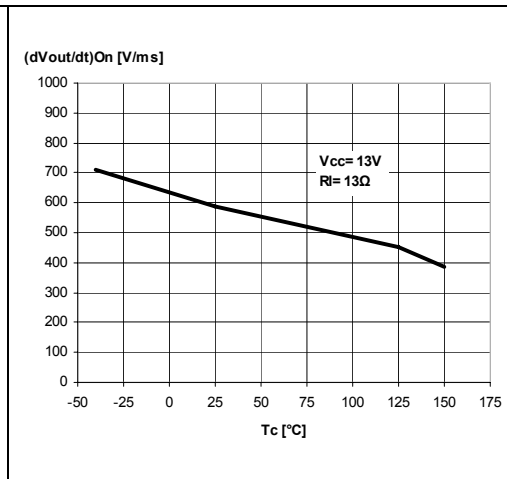


Figure 24. I_{LIMH} vs. T_{case}

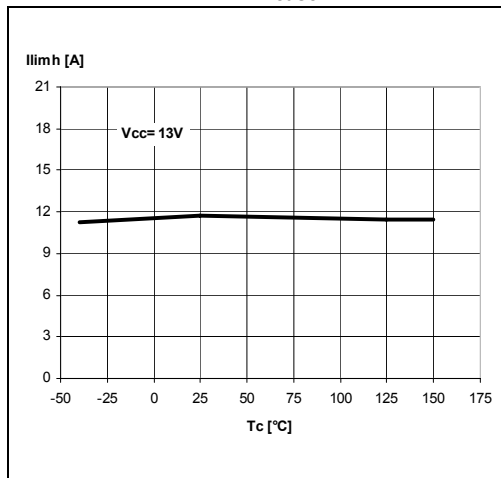


Figure 25. Turn-off voltage slope

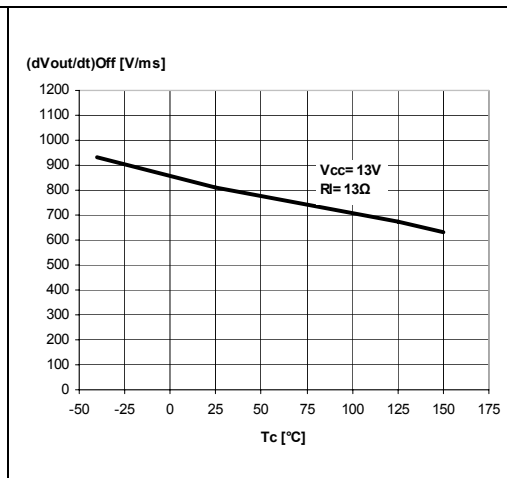


Figure 26. High-level CS_DIS voltage

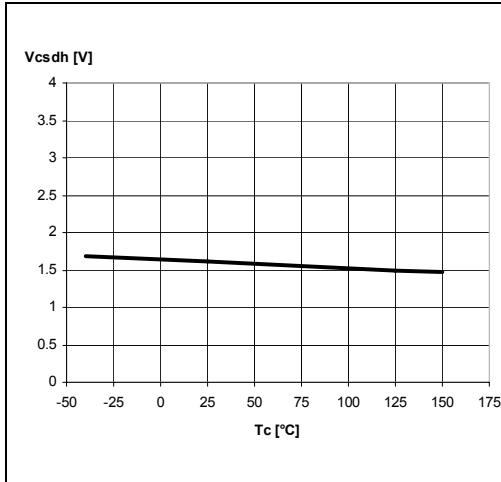


Figure 27. CS_DIS voltage clamp

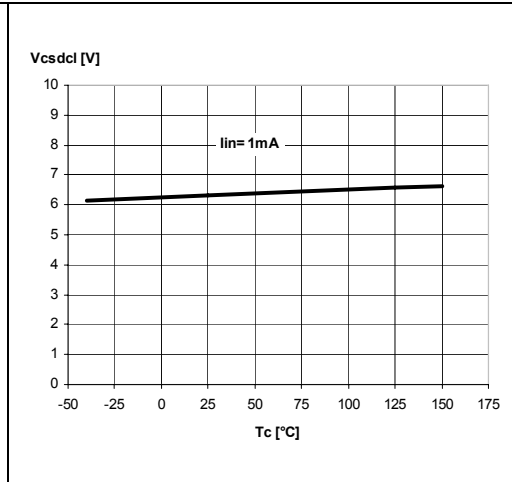
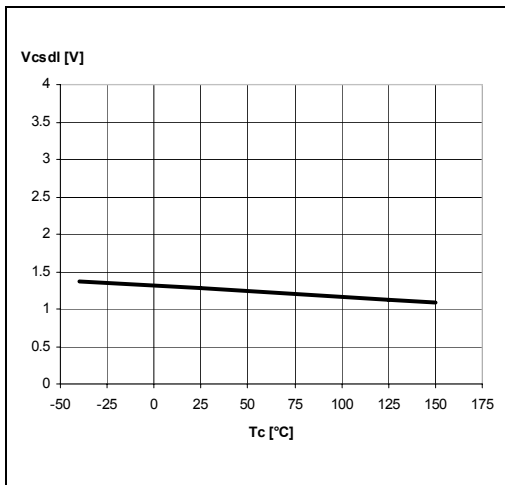
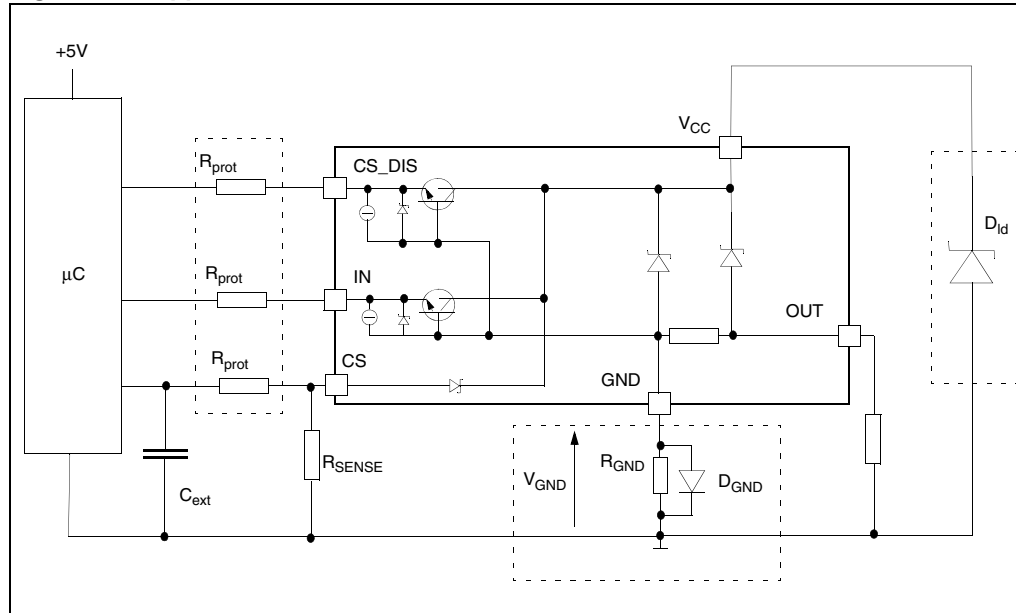


Figure 28. Low-level CS_DIS voltage



3 Application information

Figure 29. Application schematic



3.1 GND protection network against reverse battery

3.1.1 Solution 1: resistor in the ground line (R_{GND} only)

This can be used with any type of load.

The following is an indication on how to dimension the R_{GND} resistor.

1. $R_{GND} \leq 600 \text{ mV} / (I_{S(on)max})$.
2. $R_{GND} \geq (-V_{CC}) / (-I_{GND})$

where $-I_{GND}$ is the DC reverse ground pin current and can be found in the absolute maximum rating section of the device datasheet.

Power dissipation in R_{GND} (when $V_{CC} < 0$: during reverse battery situations) is:

Equation 1

$$P_D = (-V_{CC})^2 / R_{GND}$$

This resistor can be shared amongst several different HSDs. Please note that the value of this resistor should be calculated with formula (1) where $I_{S(on)max}$ becomes the sum of the maximum ON-state currents of the different devices.

Please note that if the microprocessor ground is not shared by the device ground then the R_{GND} produces a shift ($I_{S(on)max} * R_{GND}$) in the input thresholds and the status output

values. This shift varies depending on how many devices are ON in the case of several high-side drivers sharing the same R_{GND} .

If the calculated power dissipation leads to a large resistor or several devices have to share the same resistor then ST suggests to utilize Solution 2 (see [Section 3.1.2: Solution 2: a diode \(DGND\) in the ground line](#)).

3.1.2 Solution 2: a diode (D_{GND}) in the ground line

A resistor ($R_{GND} = 1 \text{ k}\Omega$) should be inserted in parallel to D_{GND} if the device drives an inductive load.

This small signal diode can be safely shared amongst several different HSDs. Also in this case, the presence of the ground network produces a shift ($\approx 600 \text{ mV}$) in the input threshold and in the status output values if the microprocessor ground is not common to the device ground. This shift not varies if more than one HSD shares the same diode/resistor network.

3.2 Load dump protection

D_{ld} is necessary (voltage transient suppressor) if the load dump peak voltage exceeds the V_{CC} max DC rating. The same applies if the device is subject to transients on the V_{CC} line that are greater than the ones shown in the ISO T/R 7637/1 table.

3.3 MCU I/Os protection

If a ground protection network is used and negative transients are present on the V_{CC} line, the control pins is pulled negative. ST suggests to insert a resistor (R_{prot}) in line to prevent the microcontroller I/Os pins to latch-up.

The value of these resistors is a compromise between the leakage current of microcontroller and the current required by the HSD I/Os (input levels compatibility) with the latch-up limit of microcontroller I/Os.

Equation 2

$$-V_{CCpeak} / I_{latchup} \leq R_{prot} \leq (V_{OH\mu C} - V_{IH} - V_{GND}) / I_{IHmax}$$

Calculation example:

For $V_{CCpeak} = -100 \text{ V}$, $I_{latchup} \geq 20 \text{ mA}$, $V_{OH\mu C} \geq 4.5 \text{ V}$

$$5 \text{ k}\Omega \leq R_{prot} \leq 180 \text{ k}\Omega.$$

Recommended values: $R_{prot} = 10 \text{ k}\Omega$, $C_{EXT} = 10 \text{ nF}$.

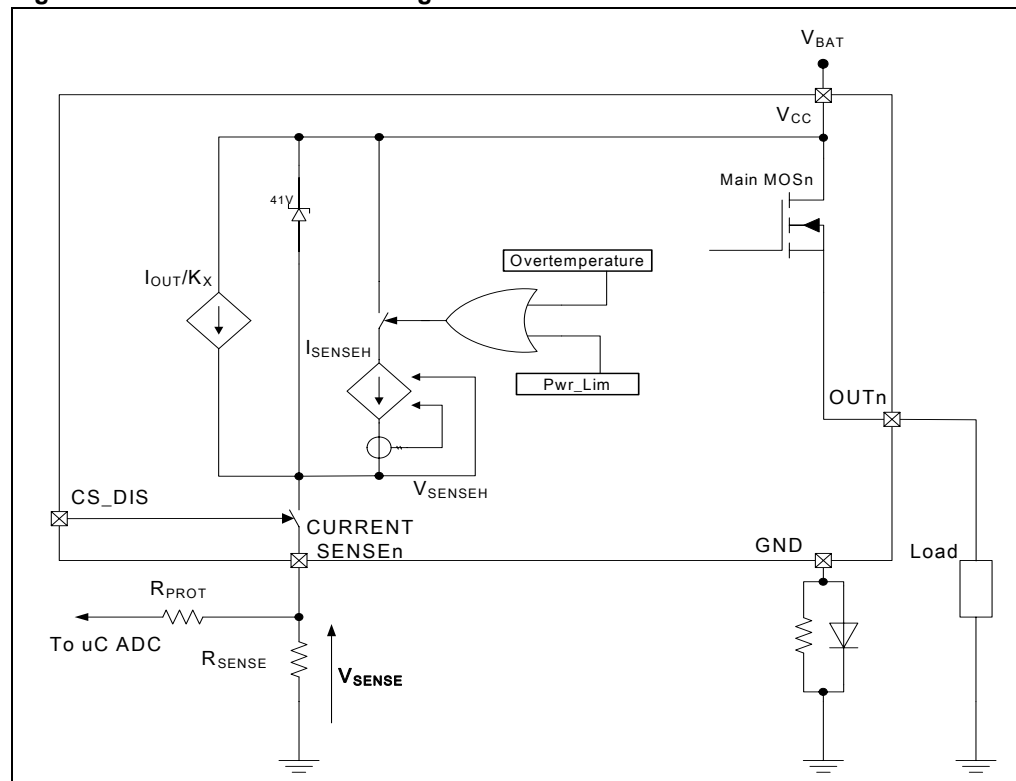
3.4 Current sense and diagnostic

The current sense pin performs a double function (see [Figure 30: Current sense and diagnostic](#)):

- **Current mirror of the load current in normal operation**, delivering a current proportional to the load one according to a know ratio K_x .
The current I_{SENSE} can be easily converted to a voltage V_{SENSE} by means of an external resistor R_{SENSE} . Linearity between I_{OUT} and V_{SENSE} is ensured up to 5 V minimum (see parameter V_{SENSE} in [Table 9: Current sense \(8 V < \$V_{CC}\$ < 18 V\)](#)). The current sense accuracy depends on the output current (refer to current sense electrical characteristics [Table 9: Current sense \(8 V < \$V_{CC}\$ < 18 V\)](#)).
- **Diagnostic flag in fault conditions**, delivering a fixed voltage V_{SENSEH} up to a maximum current I_{SENSEH} in case of the following fault conditions (refer to [Table 10: Truth table](#)):
 - Power limitation activation
 - Overtemperature

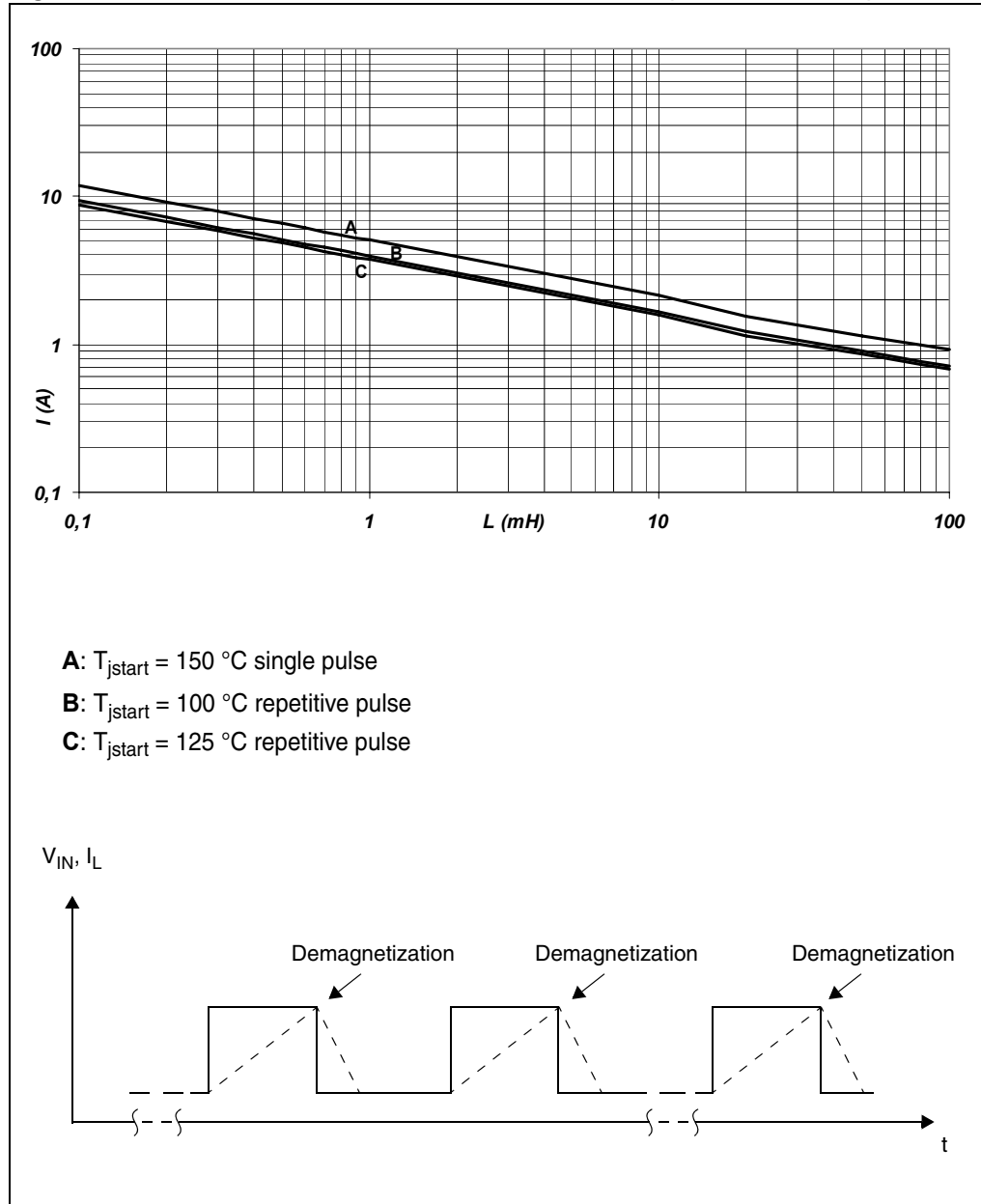
A logic high-level on CS_DIS pin sets at the same time all the current sense pins of the devices in a high-impedance-state, thus disabling the current monitoring and diagnostic detection. This feature allows multiplexing of the microcontroller analog inputs by sharing of sense resistance and ADC line among different devices.

Figure 30. Current sense and diagnostic



3.5 Maximum demagnetization energy ($V_{CC} = 13.5\text{ V}$)

Figure 31. Maximum turn-off current versus inductance (for each channel)⁽¹⁾



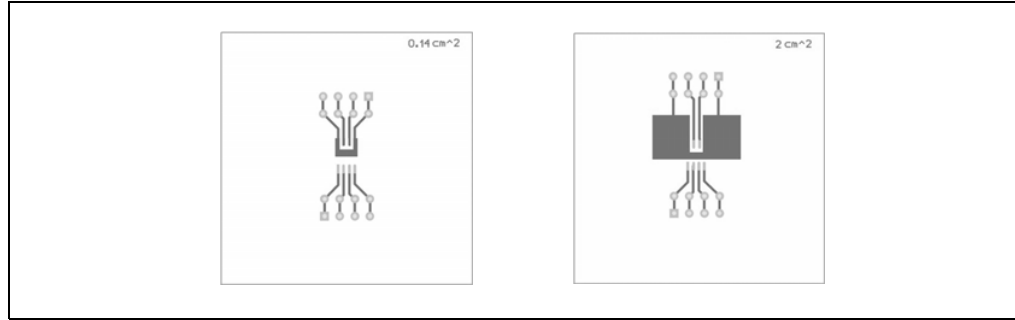
1. Values are generated with $R_L = 0\ \Omega$.

In case of repetitive pulses, T_{jstart} (at beginning of each demagnetization) of every pulse must not exceed the temperature specified above for curves A and B.

4 Package and PCB thermal data

4.1 SO-8 thermal data

Figure 32. SO-8 PC board⁽¹⁾



1. Layout condition of R_{th} and Z_{th} measurements (PCB: FR4 area = 4.8 mm x 4.8 mm, PCB thickness = 2 mm, Cu thickness = 35 μ m, Copper areas: from minimum pad lay-out to 2 cm²).

Figure 33. $R_{thj-amb}$ vs. PCB copper area in open box free air condition

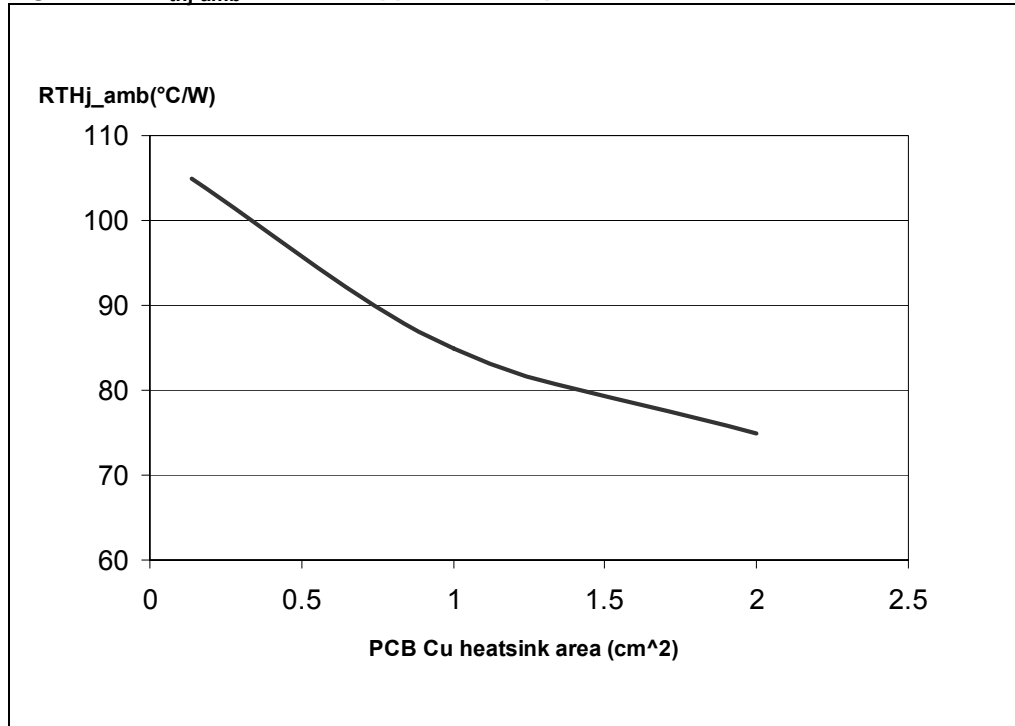
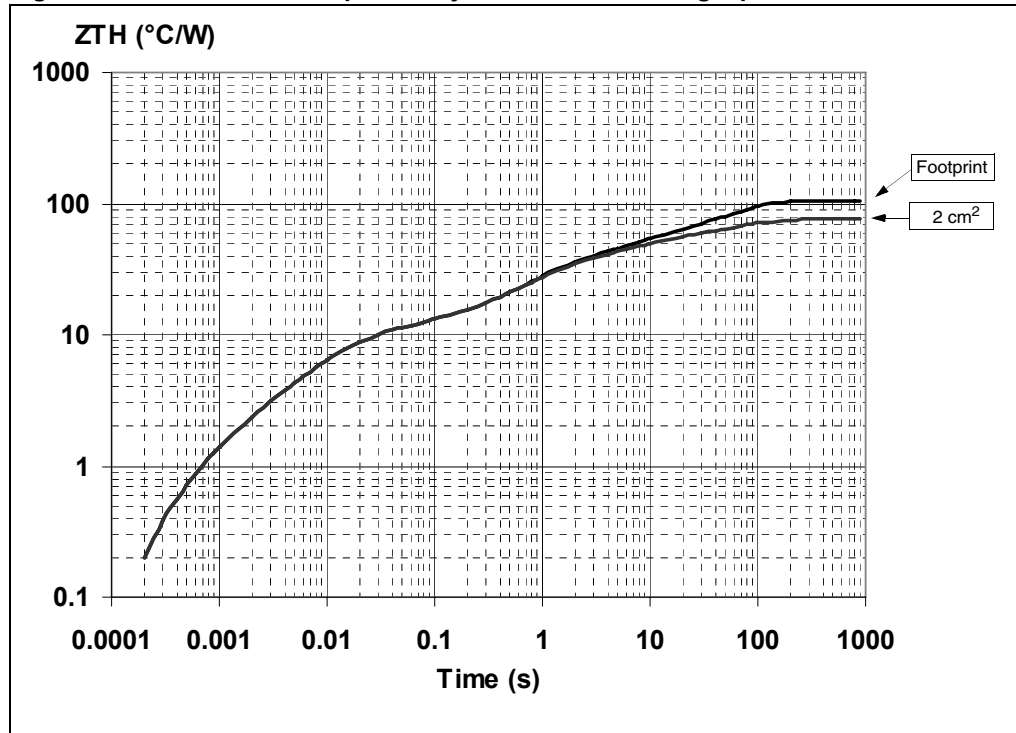


Figure 34. SO-8 thermal impedance junction ambient single pulse

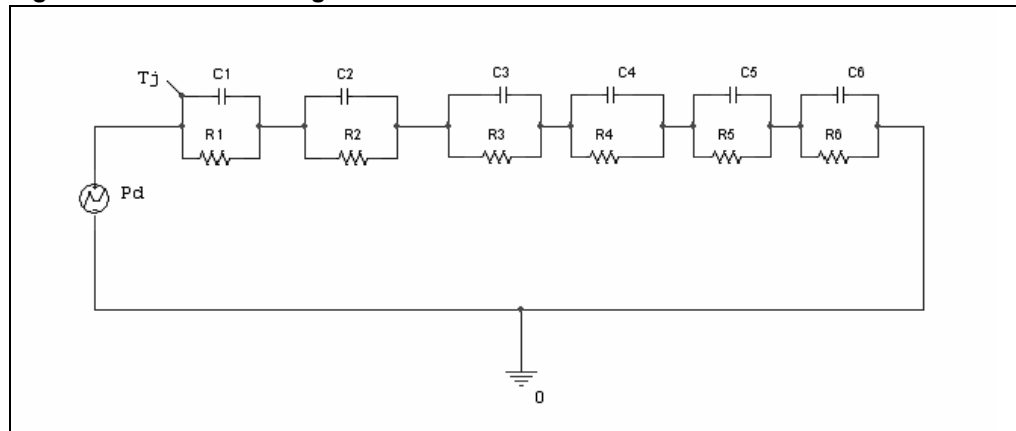


Equation 3: pulse calculation formula

$$Z_{TH\delta} = R_{TH} \cdot \delta + Z_{THtp}(1 - \delta)$$

where $\delta = t_p/T$

Figure 35. Thermal fitting model of an HSD in SO-8⁽¹⁾



1. The fitting model is a simplified thermal tool and is valid for transient evolutions where the embedded protections (power limitation or thermal cycling during thermal shutdown) are not triggered.

Table 14. Thermal parameters

| Area/island (cm ²) | Footprint | 2 |
|--------------------------------|-----------|----|
| R1 (°C/W) | 1.2 | |
| R2 (°C/W) | 6 | |
| R3 (°C/W) | 3.5 | |
| R4 (°C/W) | 21 | |
| R5 (°C/W) | 16 | |
| R6 (°C/W) | 58 | 28 |
| C1 (W.s/°C) | 0.0008 | |
| C2 (W.s/°C) | 0.0016 | |
| C3 (W.s/°C) | 0.0075 | |
| C4 (W.s/°C) | 0.045 | |
| C5 (W.s/°C) | 0.35 | |
| C6 (W.s/°C) | 1.05 | 25 |

5 Package and packing information

5.1 ECOPACK®

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

5.2 Package mechanical data

Figure 36. SO-8 package dimensions

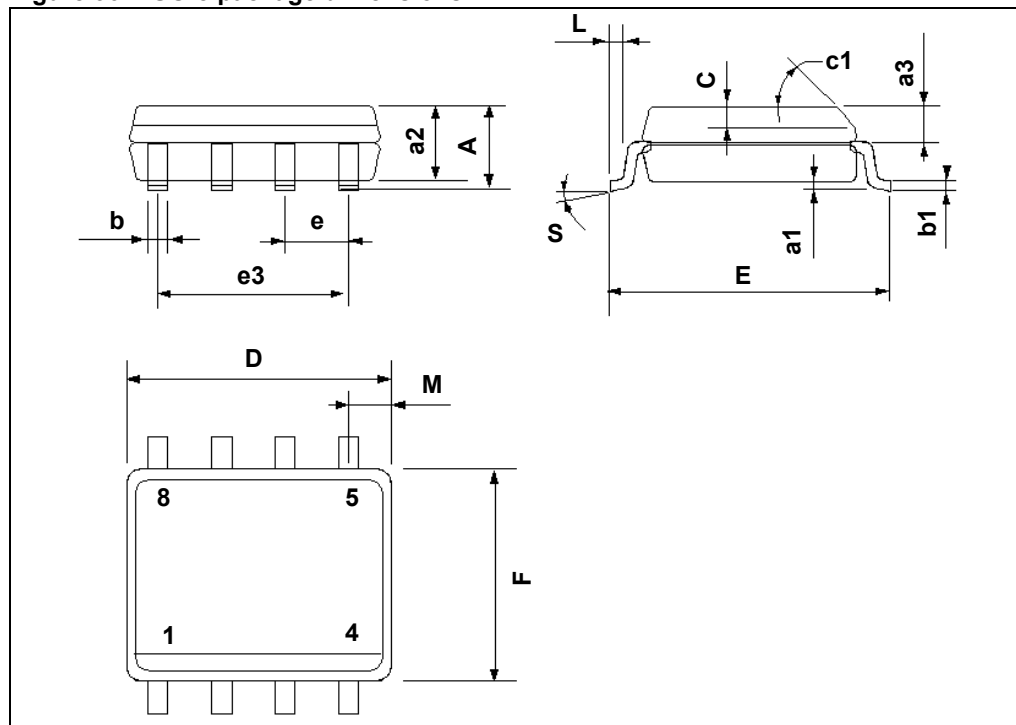


Table 15. SO-8 mechanical data

| Dim. | mm. | | |
|------|-----------|------|------|
| | Min. | Typ. | Max. |
| A | | | 1.75 |
| a1 | 0.1 | | 0.25 |
| a2 | | | 1.65 |
| a3 | 0.65 | | 0.85 |
| b | 0.35 | | 0.48 |
| b1 | 0.19 | | 0.25 |
| C | 0.25 | | 0.5 |
| c1 | 45 (typ.) | | |
| D | 4.8 | | 5 |
| E | 5.8 | | 6.2 |
| e | | 1.27 | |
| e3 | | 3.81 | |
| F | 3.8 | | 4 |
| L | 0.4 | | 1.27 |
| M | | | 0.6 |
| S | 8 (max.) | | |
| L1 | 0.8 | | 1.2 |

5.3 Packing information

Figure 37. SO-8 tube shipment (no suffix)

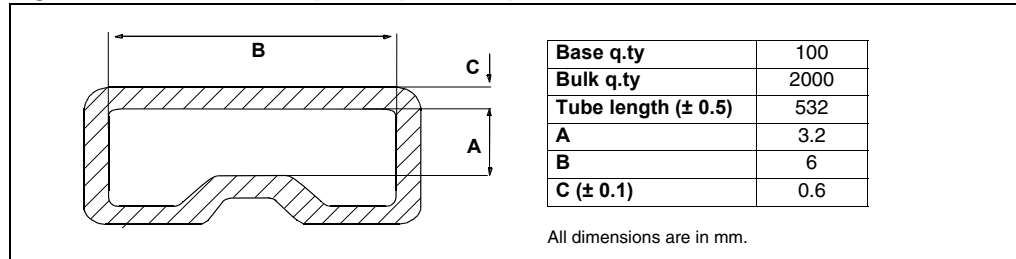
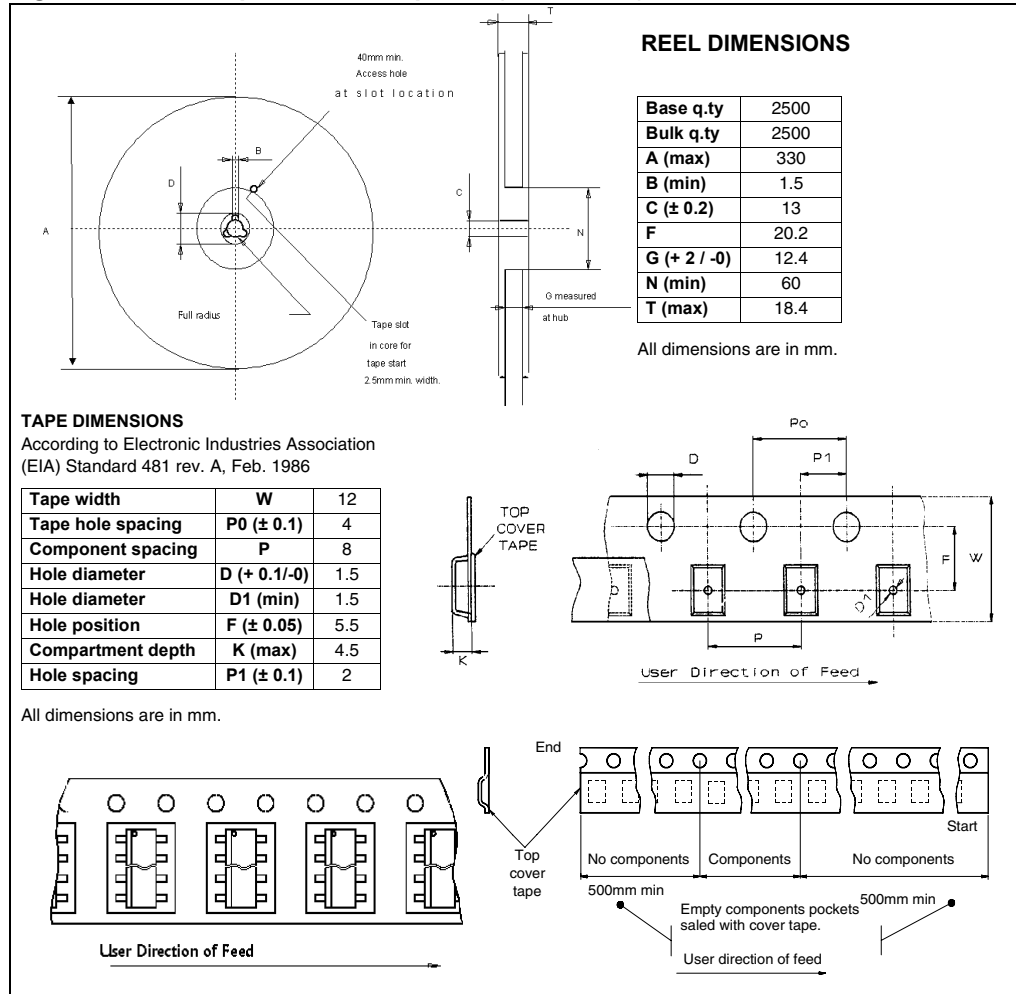


Figure 38. SO-8 tape and reel shipment (suffix "TR")



6 Order codes

Table 16. Device summary

| Package | Order codes | |
|---------|-------------|---------------|
| | Tube | Tape and reel |
| SO-8 | VN5E160MS-E | VN5E160MSTR-E |

7 Revision history

Table 17. Document revision history

| Date | Revision | Changes |
|-------------|----------|---|
| 10-Jun-2009 | 1 | Initial release. |
| 25-Jan-2010 | 2 | Updated Table 9: Current sense ($8\text{ V} < V_{CC} < 18\text{ V}$). |

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